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The invention relates to oxide semiconductor equipment and technology, in particular to methods for producing *n*-butanol sensors based on a ZnO-Al<sub>2</sub>O<sub>3</sub> heterojunction.

The method, according to the invention, comprises the deposition of a nanostructured ZnO film on a glass substrate by chemical synthesis from a solution, deposition of a Al<sub>2</sub>O<sub>3</sub> film on a ZnO film of a thickness of 17...20 nm, by vacuum thermal evaporation of aluminum triisopropylate (Al(C<sub>3</sub>H<sub>7</sub>O)<sub>3</sub>) at the substrate temperature of 450°C, deposition on the Al<sub>2</sub>O<sub>3</sub> film of meander-shaped ohmic Au-Cr contacts, fast photon processing of the resulting structure at a temperature of 650°C for 30 s.

Claims: 1

Fig.: 3